NSN 5961-00-823-9586

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-823-9586 **Inclosure Material:** Metal **Overall Length:** 7.500 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-64 **Mounting Method:** Threaded stud **Overall Width Across Flats:** 1.062 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 repetitive peak reverse voltage and 720.0 nonrepetitive peak reverse voltage and 600.0 breakover voltage, dc **Current Rating Per Characteristic:** 3.00 milliamperes forward current, average peak **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab w/wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: